

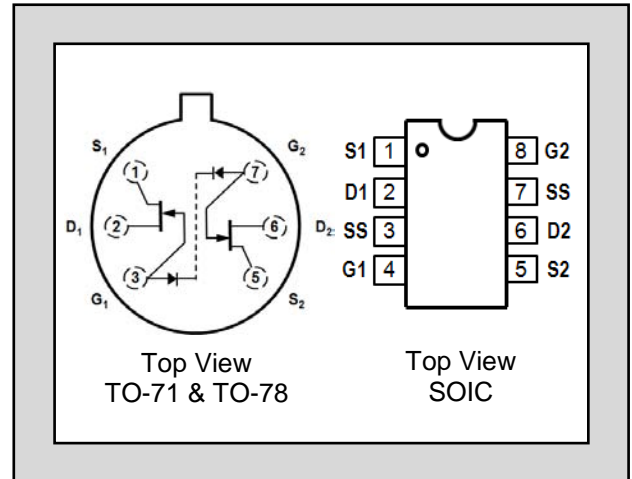
LINEAR SYSTEMS

Twenty-Five Years Of Quality Through Innovation

LS3954A LS3954 LS3955 LS3956 LS3958

LOW NOISE LOW DRIFT
MONOLITHIC DUAL N-CHANNEL
JFET AMPLIFIER

FEATURES	
LOW DRIFT	$ dV_{GS1-2}/dT = 5\mu V/^{\circ}C$ max.
LOW LEAKAGE	$I_G = 20pA$ TYP.
LOW NOISE	$e_n = 10Nv/\sqrt{Hz}$ TYP.
ABSOLUTE MAXIMUM RATINGS ¹ @ 25 °C (unless otherwise noted)	
Maximum Temperatures	
Storage Temperature	-55 to +150°C
Operating Junction Temperature	-55 to +150°C
Maximum Voltage and Current for Each Transistor ¹	
-V _{GSS}	Gate Voltage to Drain or Source 60V
-I _{G(f)}	Gate Forward Current 50mV
Maximum Power Dissipation	
Device Dissipation @ Free Air - Total	400mW @ 25°C ²

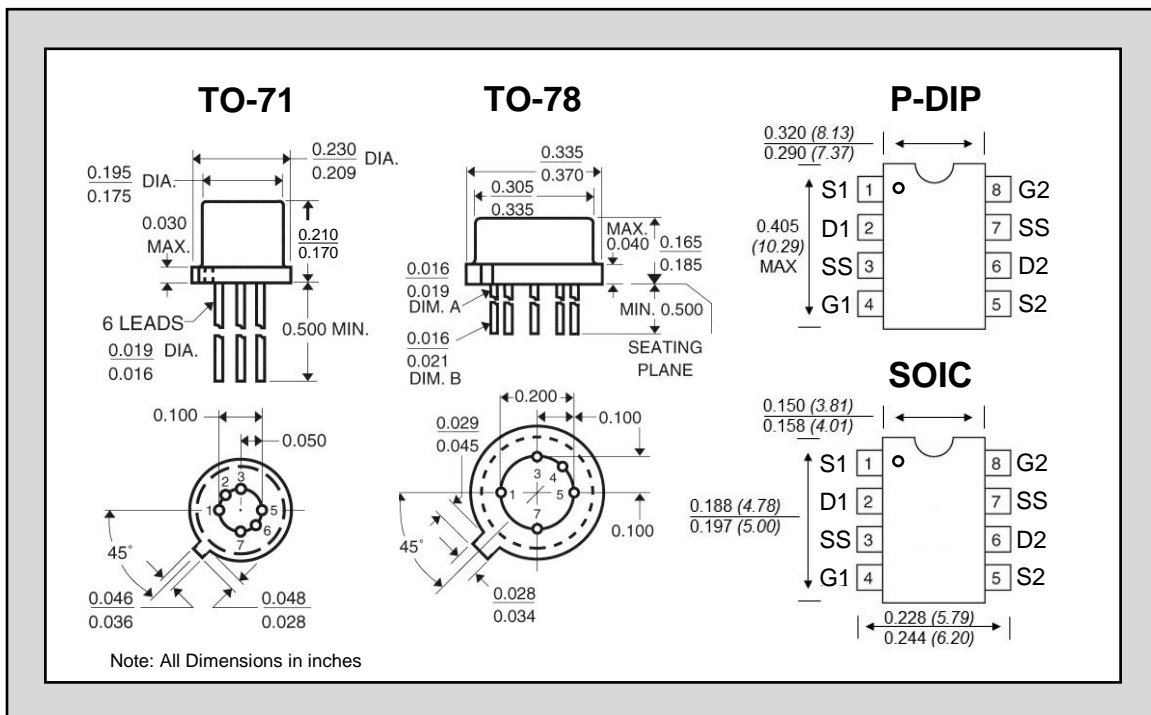


ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	LS3954A	LS3954	LS3955	LS3956	LS3958	UNITS	CONDITIONS
$ dV_{GS1-2}/dT $ max.	Drift vs. Temperature	5	10	25	50	100	$\mu V/^{\circ}C$	$V_{DG} = 20V, I_D = 200\mu A$ $T_A = -55^{\circ}C$ to $+125^{\circ}C$
$ V_{GS1-2} $ max.	Offset Voltage	5	5	10	15	25	mV	$V_{DG} = 20V, I_D = 200\mu A$

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNITS	CONDITIONS
BV _{GSS}	Breakdown Voltage	60	--	--	V	$V_{DS} = 0$ $I_G = 1\mu A$
BV _{GGO}	Gate-to-Gate Breakdown	60	--	--	V	$I_{GG} = \pm 1\mu A$ $I_D = 0$ $I_S = 0$
TRANSCONDUCTANCE						
g_{fss}	Full Conduction	1000	2000	4000	μS	$V_{DG} = 20V$ $V_{GS} = 0$ $f = 1kHz$
g_{fs}	Typical Operation	500	700	1250	μS	$V_{DG} = 20V$ $I_D = 200\mu A$
$ g_{fs1-2}/g_{fs} $	Differential	--	± 0.6	± 3	%	
DRAIN CURRENT						
I_{DSS}	Full Conduction	0.5	2	5	mA	$V_{DS} = 20V$ $V_{GS} = 0$
$ I_{DSS1-2}/I_{DSS} $	Differential	--	± 1	± 5	%	
GATE VOLTAGE						
$V_{GS(off)}$	Pinchoff Voltage	-1	-2	-4.5	V	$V_{DS} = 20V$ $I_D = 1nA$
V_{GS}	Operating Range	-0.5	--	-4	V	$V_{DS} = 20V$ $I_D = 200\mu A$
GATE CURRENT						
-I _G	Operating	--	20	50	pA	$V_{DG} = 20V$ $I_D = 200\mu A$
-I _G	High Temperature	--	--	50	nA	$V_{DG} = 20V$ $I_D = 200\mu A$ $T_A = +125^{\circ}C$
-I _G	Reduced V _{DG}	--	5	--	pA	$V_{DG} = 10V$ $I_D = 200\mu A$
-I _{GSS}	At Full Conduction	--	--	100	pA	$V_{DG} = 20V$ $V_{DS} = 0$

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNITS	CONDITIONS
OUTPUT CONDUCTANCE						
g_{oss}	Full Conduction	--	--	35	μS	$V_{DG}=20V$ $V_{GS}=0$
g_{os}	Operating	--	0.5	1	μS	$V_{DG}=20V$ $I_D=200\mu A$
$ g_{os1-2} $	Differential	--	0.05		μS	
COMMON MODE REJECTION						
CMRR	$-20 \log \Delta V_{GS1-2}/\Delta V_{DS} $	--	100	--	dB	$\Delta V_{DS}=10$ to $20V$ $I_D=200\mu A$
CMRR	$-20 \log \Delta V_{GS1-2}/\Delta V_{DS} $	--	75	--	dB	$\Delta V_{DS}=5$ to $10V$ $I_D=200\mu A$
NOISE						
NF	Figure	--	--	0.5	dB	$V_{DS}=20V$ $V_{GS}=0$ $R_G=10M\Omega$ $f=100Hz$ $NBW=6Hz$
e_n	Voltage	--	--	15	nV/\sqrt{Hz}	$V_{DS}=20V$ $I_D=200\mu A$ $f=10Hz$ $NBW=1Hz$
CAPACITANCE						
C_{ISS}	Input	--	--	6	pF	$V_{DS}=20V$ $V_{GS}=0$ $f=1MHz$
C_{RSS}	Reverse Transfer	--	--	2	pF	
C_{DD}	Drain-to-Drain	--	0.1	--	pF	$V_{DG}=20V$ $I_D=200\mu A$



NOTES:

1. These ratings are limiting values above which the serviceability of any semiconductor may be impaired.
2. Derate $4mW/^\circ C$ above $25^\circ C$

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